

RJK6054DPP-M0

Silicon N Channel MOS FET High Speed Power Switching

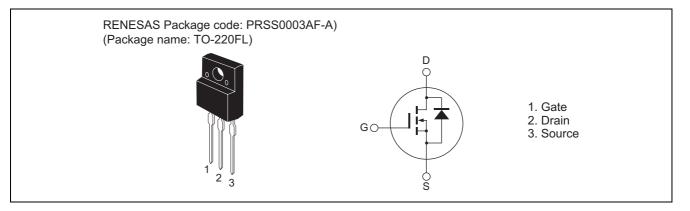
> REJ03G1801-0100 Rev.1.00 Jul 02, 2009

> > $(T_0 - 25^{\circ}C)$

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(1a = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID Note4	16	А
Drain peak current	Note1 ID (pulse)	32	А
Body-drain diode reverse drain current	I _{DR}	16	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	32	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.87	mJ
Channel dissipation	Pch Note2	35	W
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25° C

- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area



Electrical Characteristics

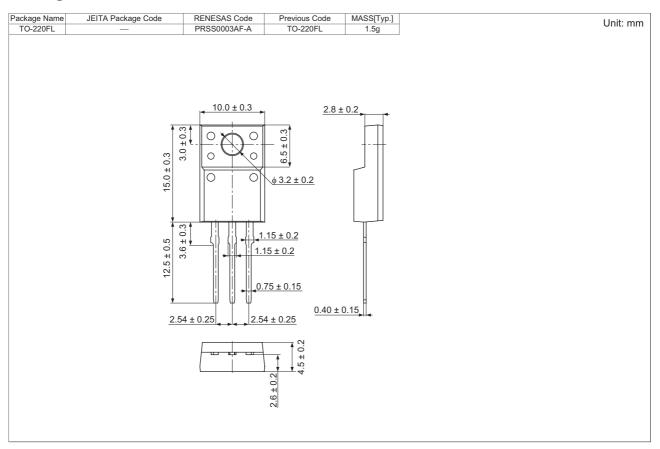
 $(Ta = 25^{\circ}C)$

ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	0.475	0.720	Ω	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
resistance	0.		4700		_	<u>)// 05.)/</u>
Input capacitance	Ciss		1730	_	pF	$V_{DS} = 25 V$
Output capacitance	Coss	—	175	—	pF	$V_{GS} = 0$ f = 1 MHz
Reverse transfer capacitance	Crss	_	21	_	pF	
Turn-on delay time	t _{d(on)}	_	35	—	ns	$I_{D} = 8 A V_{GS} = 10 V R_{L} = 37.5 \Omega Rg = 10 \Omega$
Rise time	tr	_	22	—	ns	
Turn-off delay time	t _{d(off)}	_	88	—	ns	
Fall time	t _f	_	18	—	ns	
Total gate charge	Qg	_	45	—	nC	$V_{DD} = 480 V$ $V_{GS} = 10 V$ $I_D = 16 A$
Gate to source charge	Qgs	_	8.7	—	nC	
Gate to drain charge	Qgd		20.8		nC	
Body-drain diode forward voltage	V _{DF}	_	0.91	1.50	V	$I_F = 16 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}	_	330		ns	$I_F = 16 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 5. Pulse test



Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJK6054DPP-M0-T2	1050 pcs	Box (Tube)



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